Abstracts

A Miniature 2-18 GHz Monolithic GaAs Distributed Amplifier

W. Kennan, T. Andrade and C. Huang. "A Miniature 2-18 GHz Monolithic GaAs Distributed Amplifier." 1984 Microwave and Millimeter-Wave Monolithic Circuits Symposium Digest 84.1 (1984 [MCS]): 41-44.

A 2-18 GHz monolithic GaAs distributed amplifier has been developed with over 6dB gain ± 0.5 dB gain ripple, less ttlan 2.0 input and output VSWR less than 7.5 dB noise figure, and greater than 17 dBm power output capability. The amplifier is designed with dual-gate GaAs FET's and measures .75 mm by .85 mm (.64 mm^2). The small size insures high circuit yield and makes the part cost effective for general applications.

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